

SPECIFICATION OF LED CHIP

C970-40

[INFRARED]

1) Commodity Type and Physical Characteristics.

1. Material GaAs/GaAs
2. Electrode
 - Top Side P (anode) side : Au Alloy
 - Bottom Side N (cathode) side : Au Alloy
3. Electrode Pattern Fig.1
4. Chip Size Fig.2
5. Chip Thickness Fig.2
6. Emission Area Fig.2

2) Electro-Optical Characteristics

Parameters	Symbol	Condition	min.	typ.	max.	unit
Forward Voltage	V _f	I _f =20mA		1.25	1.35	V
Reverse Current	I _r	V _r =5V			10	uA
Power Intensity	P _o	I _f =20mA	0.5	1.0		mW
Peak Wavelength	λ _P	I _f =20mA	960	970	980	nm
Spectral Radiation Bandwidth	Δλ	I _f =20mA		50		nm
RiseTime	t _r	I _f =20mA		1000		ns
FallTime	t _f	I _f =20mA		500		ns

‡ Die shall be mounted on TO=18 gold header without resin coated.(Ta=25°C)

[Unit : μm]

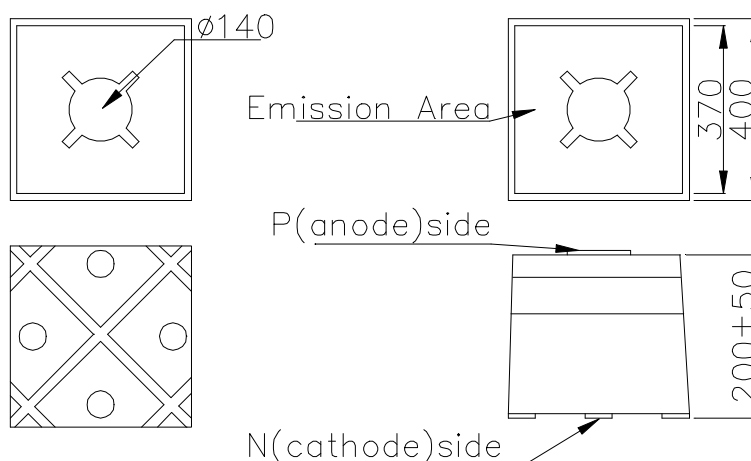


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area